

Micro and Nanotechnology Processes for the High Volume manufacture of laser targets

Bob Stevens Process Development Group Leader

Micro and Nanotechnology Centre Rutherford Appleton Laboratory



Contents

- The Micro and Nanotechnology Centre
- Examples of mass produced laser targets
- Some Processes for Volume Manufacture



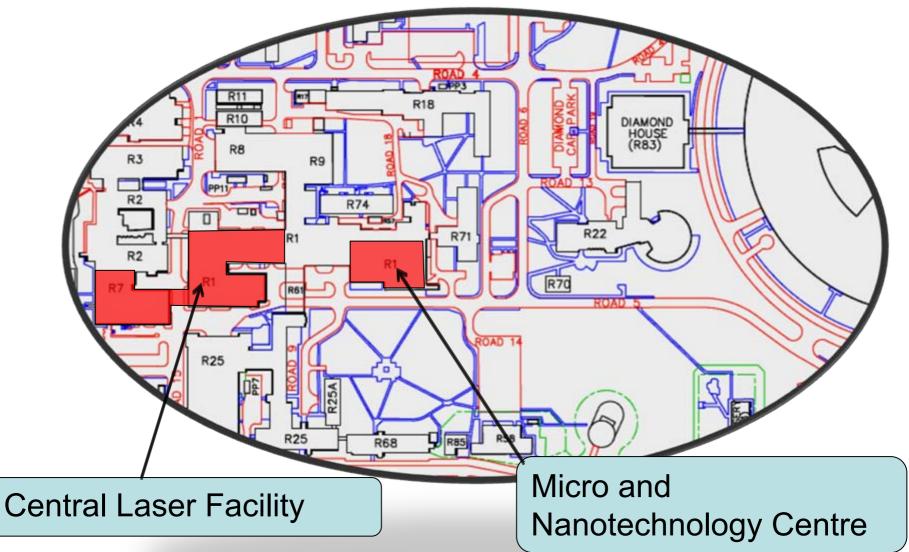
Micro and Nanotechnology Centre

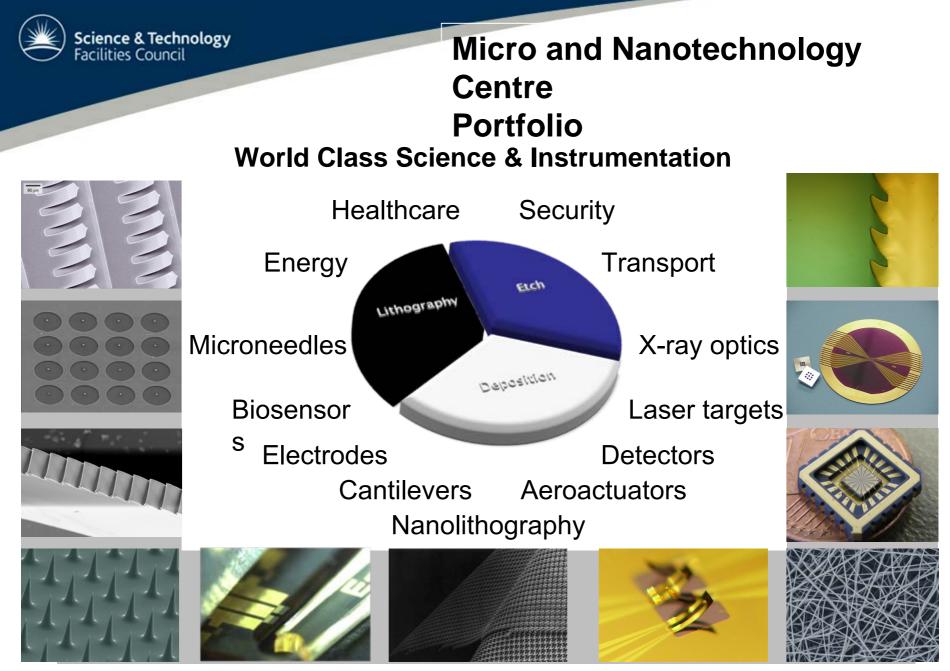
- · Launched in September 2008
- Primary strategic objective:Deliver the Micro and Nanotechnology NEEDS of STFC's Large Scale Facilities and Programmes and their user communities.
 - Photon Science Department
 - · Central Laser Facility, Lasers for Science Facility and SRS
 - ISIS
 - Diamond Light Source
 - ESRF



Location

Rutherford Appleton Laboratory





Spinouts: Microvisk, Oxsensis, ElectrospinningHosted companies: AML Qudos

MNT Centre Facilities



Lithography

- Electron Beam
- Optical (Contact and Stepper)
- Deposition
 - Thermal Oxidation
 - Plasma Enhanced CVD. Silicon, Oxides and Nitrides
 - DC Magnetron Sputtering
 - Four pocket E-Gun Evaporation with variable angle substrates
 - Wet chemical etch. (Spray and Tank processes)
- Etching
 - Reactive Ion Etch,
 - Deep RIE (Silicon, Germanium, Sapphire, Diamond**)
 - Wet Etch
- Chemical Mechanical Polishing*
- Wafer Cleaning
- Metrology and Test
- Wafer Bonding*
- Indium evaporation & Bump Bonding
- Nano Materials Development and Handling
- Electrospinning of Nano Fibres
- Electroplating Centre. (Au, In, Ni)
- Powder Blasting
- Screen and Stencil printing



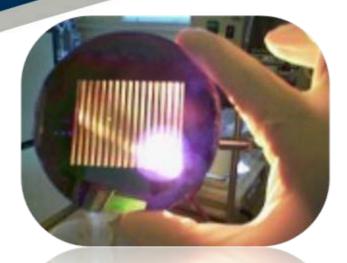




Examples of Laser targets



Multi-vane Targets



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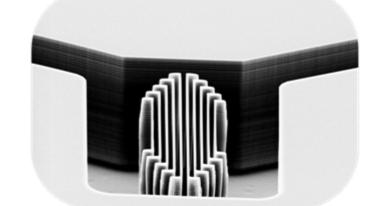
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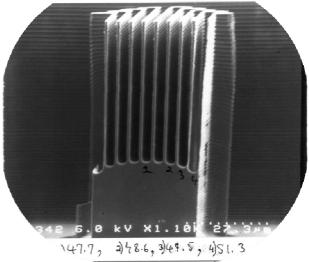
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Key processes.

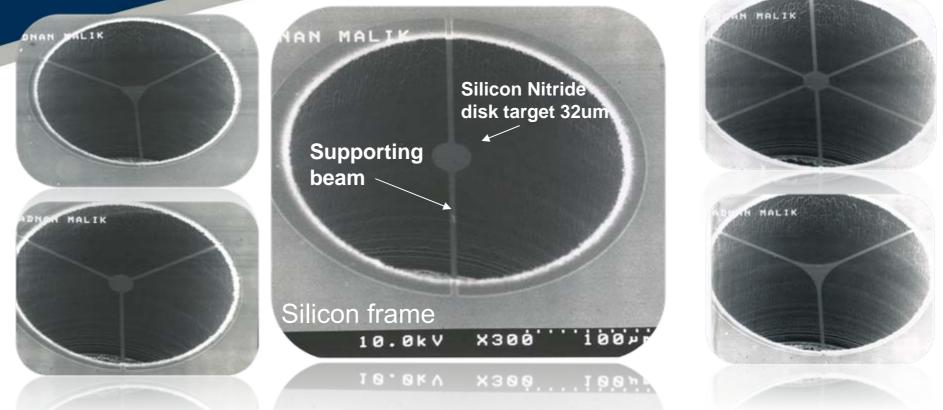
Double sided optical lithography **PECVD** Oxide **RIE Oxide Etch** HF Etch **Deep Silicon Etch**

4= 74.4 Mm





Membrane Targets

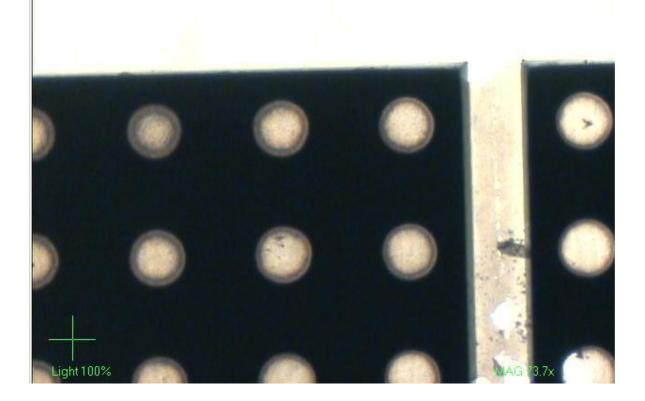


Suspended 100 nm thick Silicon Nitride Laser Targets Key Processes:

- -LPCVD Silicon Nitride and Low Temperature Oxide
- -Deep Reactive Ion Etching of Silicon
- Photolithography with backside alignment
- Reactive Ion Etching of Silicon Nitride and Oxide
- Deposition of PECVD Silicon Dioxide
- Hydrofluoric Acid Etching



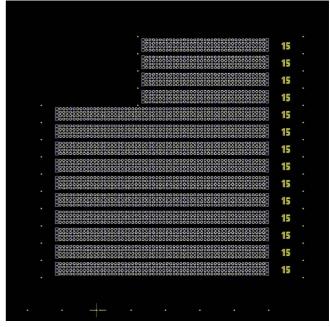
Diamond and DLC membranes





(Diamter Silicon (2um thick) 5, 10, 15, 20 um) 10um 10um Oxide (2um thick).

Disc Targets



Key Processes

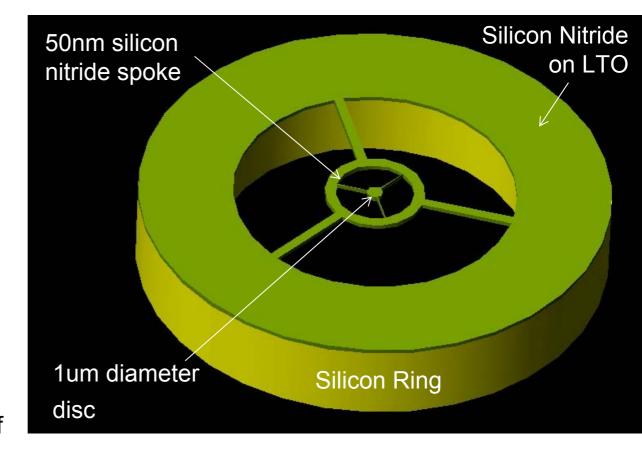
- Single sided Photolithography
- Deposition of LPCVD Silicon Nitride
- Deep Silicon Etching
- Reactive Ion Etching of Silicon Nitride and Silicon Dioxide.
- Wafer Dicing



Nanospoke Targets

Key Processes

- Deposition of LPCVD Silicon Nitride
- Deep Silicon Etch
- Photolithography with backside alignment
- Electron Beam Lithography
- Deposition of PECVD Oxide
- Reactive ion etching of Silicon dioxide and nitride
- Hydrofluoric Acid etch of silicon dioxide.





Some Processes for Volume Manufacture

- Deep Silicon Etch
- Electrospinning of Nanofibres
- · Greyscale Lithography
- Electroforming
- Atomic Layer Deposition
- Massively Parallel Assembly (Flip Chip)



Target wheel

Targets **Deep Silicon Etching** Etch chamber R.F. matching unit Turbo pump . Capacitance monometer Carousel Loadlock Carousel control system © STS Ltd

STS Deep Silicon Etch Tool





Types of Nanofibre

- Homogenious Fibres
- Core-Shell
- Core-Multishell
- Hollow
- Porous

Nanofibre materials

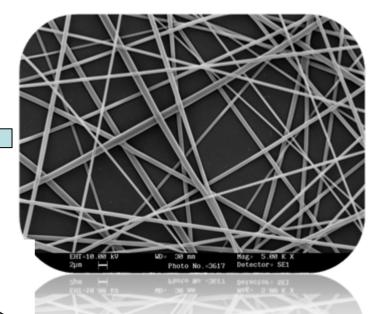
- Gelatin & Collagen
- PVA, PAN, PEG, PEO, PVDF
- Polysulfone, Polyamides, etc
- PLA, PLGA, PGA, PCL
- Carbon and Graphitised Fibre
- Nanoparticle &CNT composite



Low density, low mass nanofibre mesh for target supports

'Y' Frame made from silicon, ceramic or polymer. It would have location tag for low attachment to transfer puck & alignment fiducials for placement measurements.

Web of fibres is electrospun over the frame to form a support for the target.



Electrospun Nanocomposite Nanofibres.

Diameters 10nm to 10um



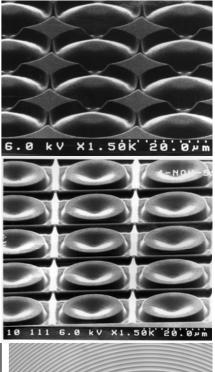
Greyscale Lithography

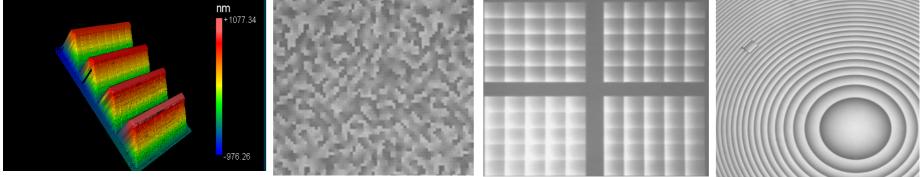
Photomasks with 512 grey levels, 0.1um resolution. OD 0.1 to 4

Production of microlenses, micro prisms.

Pattern transfer using Plasma etch and Ion Milling

Production of moulds to form greyscale components



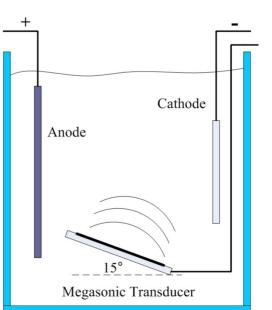


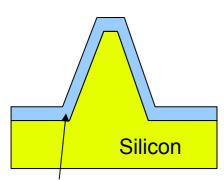


Electroforming

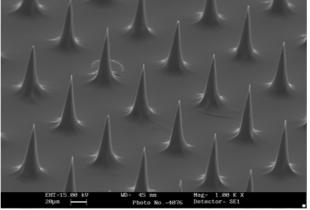
Processes

- Au, In, Ni up to 200mm wafers
- Plating Moulds (SU8, AZ9260, DRIE Silicon, etc)
- Arbitary waveform Plating supply for DC, Unipolar, Bipolar for plating of surfaces with high aspect ratio structures
- Megasonic agitation for improved process yield for fine structures.

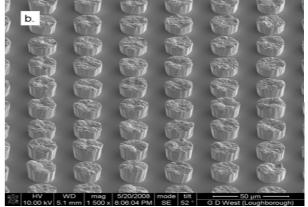




Coating defined by pulse-reverse plating



Silicon Microneedles



18um Indium Bumps



Atomic Layer Deposition

Nanolaminates, Nanocomposites and Ultra Thin structures

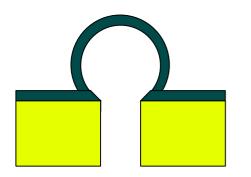
Low temperature (able to coat plastics) Pin hole free coatings. Highly Conformal (Able to coat aspect ratio of 1000:1) Extremely thin films (5nm) Single substrate or batch processing

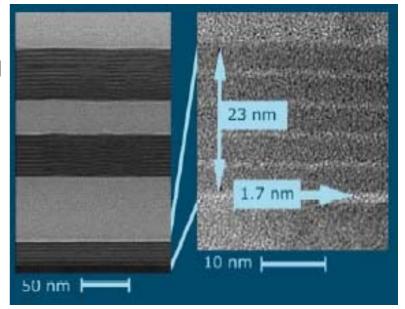
Materials

Metals Dielectrics Rare Earth doped Oxides (Phosphors)

Applications in Laser Targets.

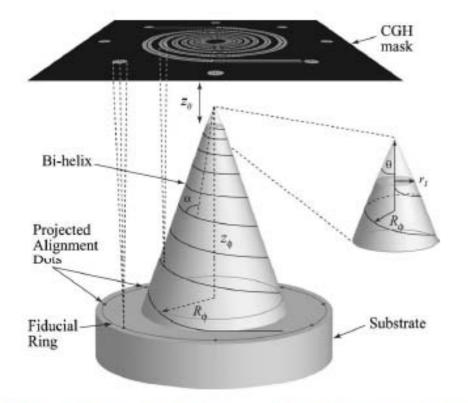
Engineering of Nanocomposite/Nanolaminate Target Materials (Elemental control) Coating of moulds to form thin wall vessels (e.g. thin walled shells, multi-layers...







Holographic Lithography



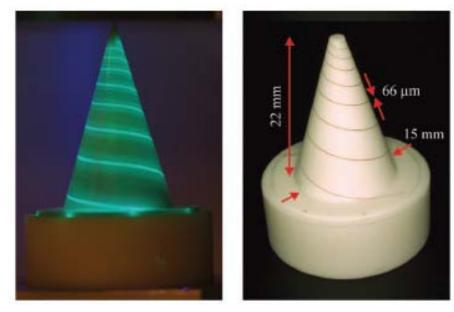


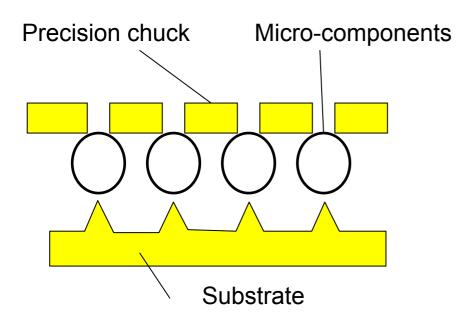
Fig. 1 Nonplanar photolithography system: θ =16.5 deg is the cone half-angle, z_0 =8.4 mm is the exposure offset, r_1 =1 mm is the initial helix radius, and α =74.2 deg is the wrap angle of the helix.

J. Micro/Nanolith. MEMS MOEMS 64, 043015 Oct–Dec 2007



Massively Parallel Assembly

Placement accuracy +/- 1 micron Heated chucks Vacuum Pick Up





FC250 Flip Chip Die Bonder



For more information contact

Bob Stevens: Micro and Nanotechnology Centre STFC

Robert.Stevens@stfc.ac.uk